

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L<sup>2</sup>-π-MOSIII)

## 2SK1382

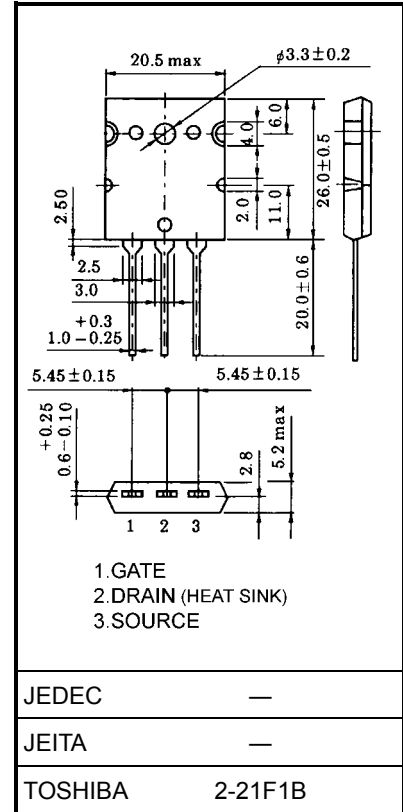
Relay Drive, Motor Drive and DC-DC Converter Applications

Unit: mm

- 4 V gate drive
- Low drain-source ON resistance :  $R_{DS(ON)} = 15 \text{ m}\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 47 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 100 \text{ V}$ )
- Enhancement-mode :  $V_{th} = 0.8\sim 2.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	100	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	100	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	60
	Pulse (Note 1)	$I_{DP}$	240
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	200	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~150	$^\circ\text{C}$



Weight: 9.75 g (typ.)

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.625	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	35.7	$^\circ\text{C} / \text{W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.  
Please handle with caution.

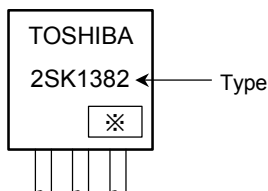
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 100$	nA
Drain cut-off current		$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	100	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 30\text{ A}$	—	20	29	m $\Omega$
			$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	—	15	20	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 30\text{ A}$	30	47	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	7000	—	pF
Reverse transfer capacitance		$C_{rss}$		—	400	—	
Output capacitance		$C_{oss}$		—	2700	—	
Switching time	Rise time	$t_r$		—	16	—	ns
	Turn-on time	$t_{on}$		—	55	—	
	Fall time	$t_f$		—	80	—	
	Turn-off time	$t_{off}$		—	280	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 80\text{ V}, V_{GS} = 10\text{ V}, I_D = 60\text{ A}$	—	176	—	nC
Gate-source charge		$Q_{gs}$		—	132	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	44	—	

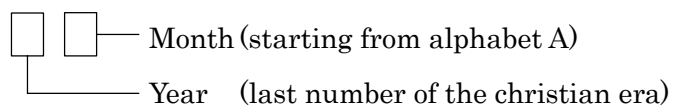
## Source-Drain Ratings and Characteristics (Ta = 25°C)

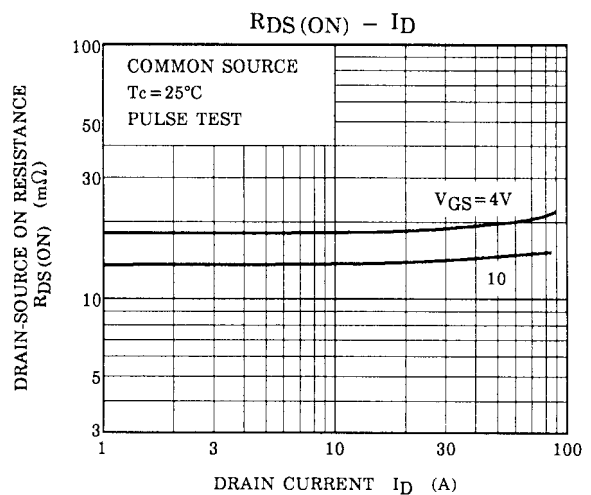
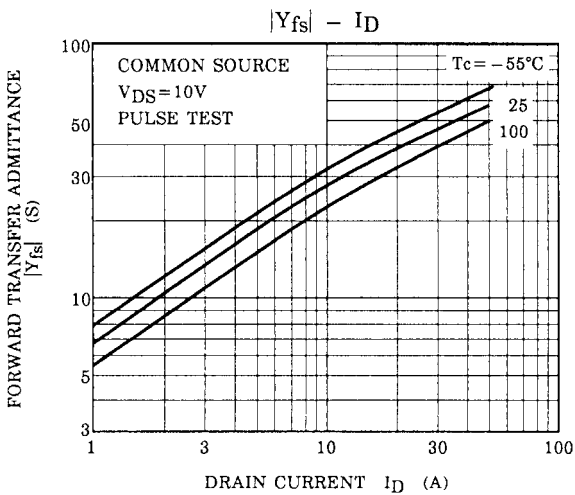
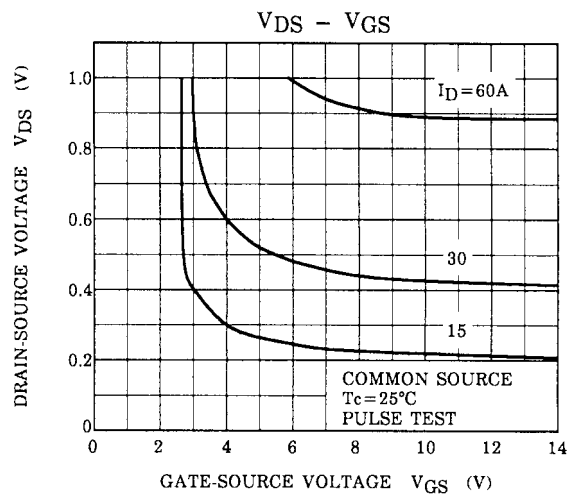
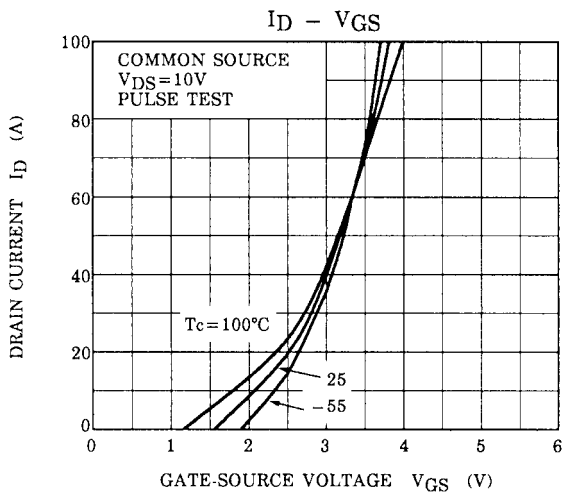
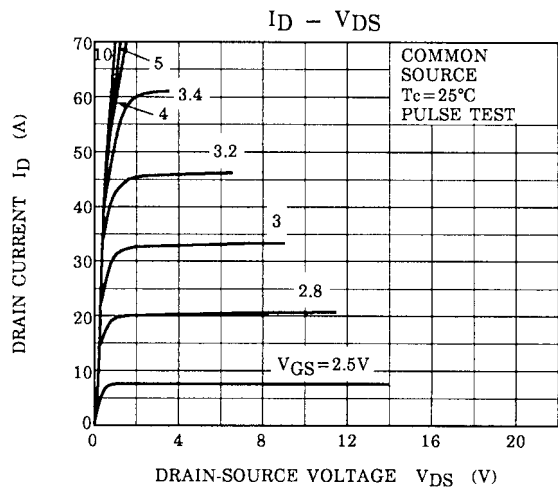
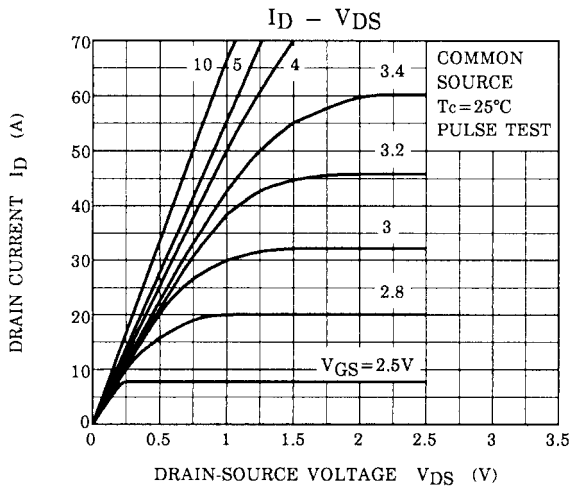
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	60	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	240	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 60\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.6	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 60\text{ A}, V_{GS} = 0\text{ V}$	—	300	—	ns
Reverse recovered charge	$Q_{rr}$	$dI_{DR} / dt = 50\text{ A} / \mu\text{s}$	—	0.75	—	$\mu\text{C}$

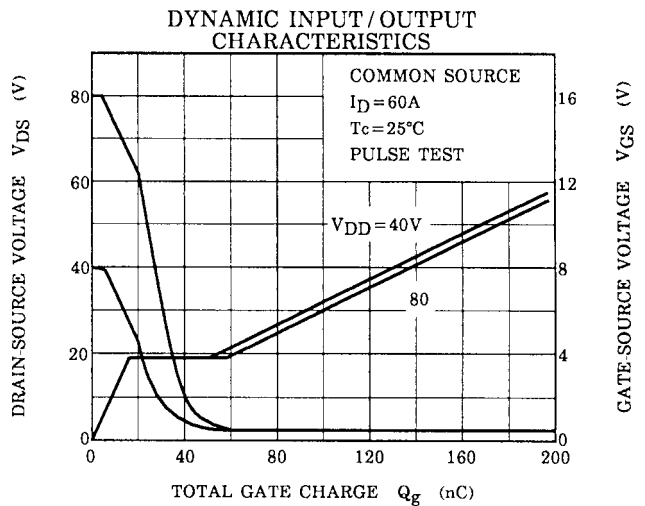
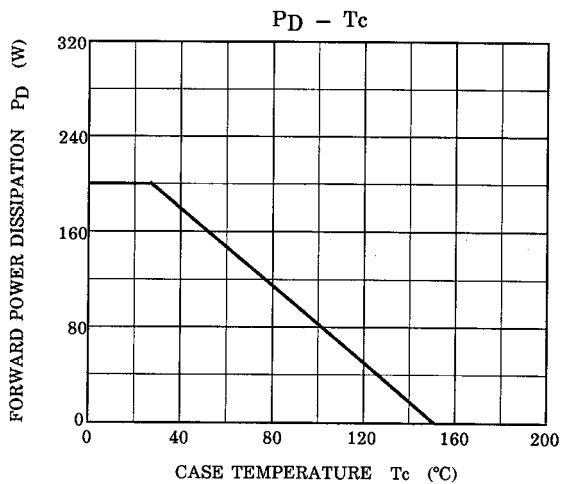
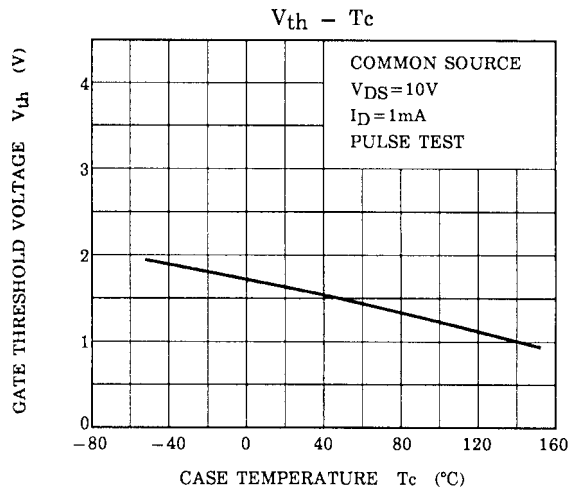
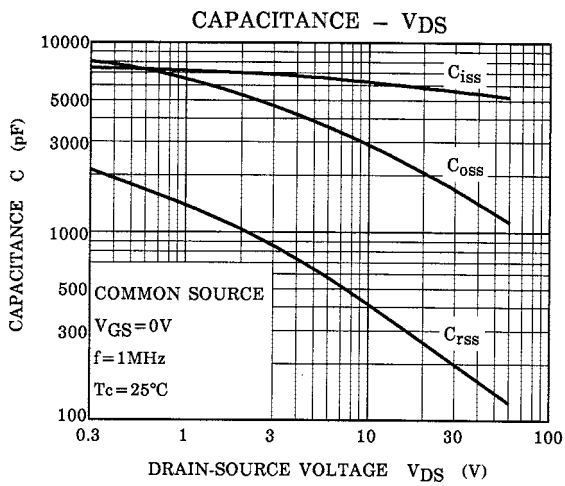
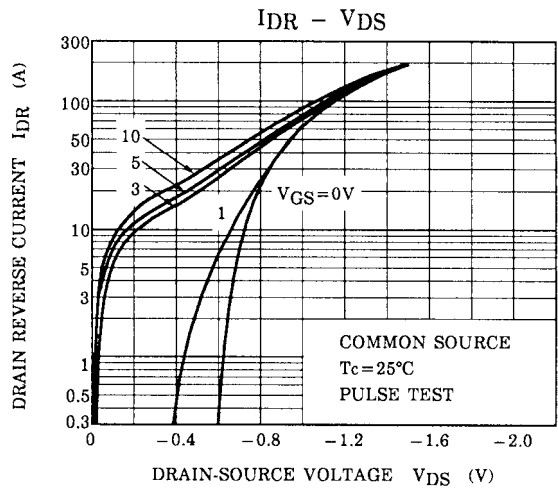
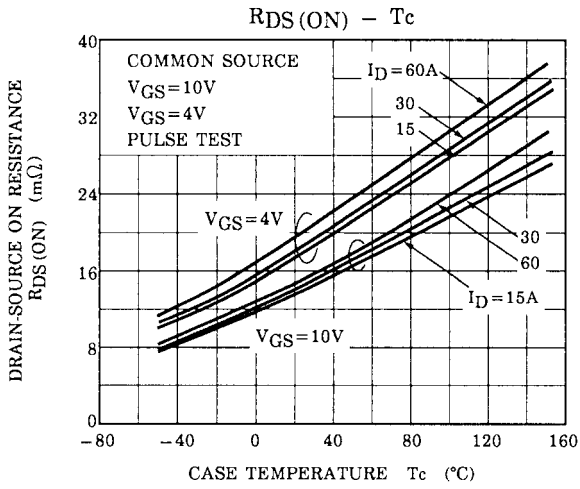
## Marking

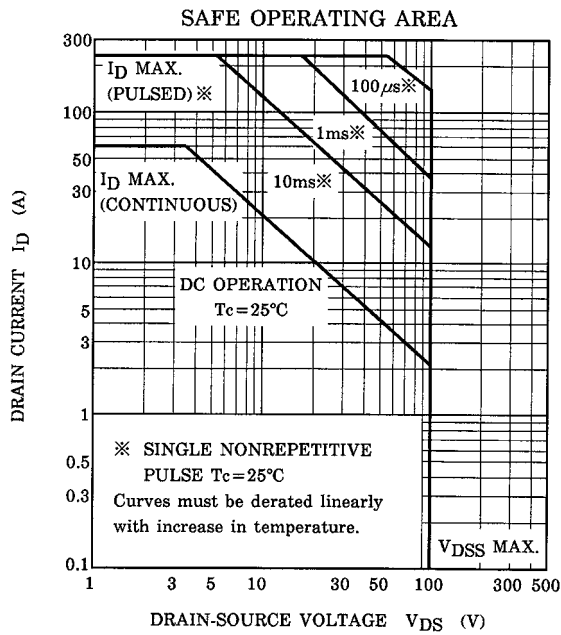
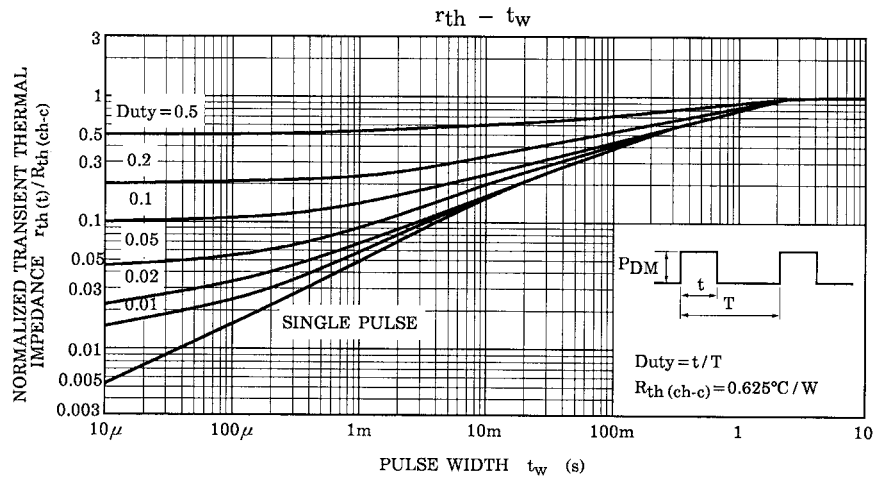


※ Lot Number









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